

CoolGaN™ e-mode HEMT



英飛凌

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Co., Ltd.**

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[Company Website](#)

Booth No. S0914



Winning Reason

- This product is an enhanced transistor that has a unique “Normal OFF” property which allows for a longer product life-span.
- This product can produce higher system efficiency, greatly increase power density and higher operating frequency.
- This product benefits from GaN technology, including high reliability and longer life-span. Also, since the power density has been greatly increased, the system costs have also been largely reduced.

Product Feature

Infineon CoolGaN™ e-mode HEMT reaches 140 W/in³ for 3kW LLC with >98% efficiency, significantly improving power density to almost 3 fold enabling more compact design and efficiency improvement.

- Features:
 1. Enhanced Mode: Unique normOFF concept solution and the best fit for longest lifetime
 2. Ultra fast switching
 3. No reverse recovery charge
 4. Capable of reverse conduction
 5. Superior commutation ruggedness

Benefits:

OPEX and CAPEX reduction, power density improvement and system cost reduction